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TI Optical recording films
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AB An optical recording film has a composition of AxBySezTem ($0 \leq x \leq 30$, $10 \leq y \leq 70$, $30 \leq z \leq 80$, $0 \leq m < 30$ atomic%, and B = **Sn** and/or **Pb**). A may be ≥1 of Zn, Cd, Hg, Al, Ga, In, **Tl**, C, Bi, B, N, P, O, S, F, lanthanide elements, actinide elements, and inert gas elements (e.g., <30 atomic%); Si, Ge, As, and Sb (e.g., <10 atomic%); and Ti, Ni, Co, Sc, Y, Zr, V, Nb, Cr, Mo, Mn, **Fe**, Ru, Rh, Pd, Ta, and Pt (e.g., <1 atomic%). The composition may have $0.3 < y/(y + z) \leq 0.4$ with $10 \leq m \leq 25$. A Si3N4 layer 40-nm thick, a Sn28Se57Te15 layer 100-nm thick, and a Si3N4 layer 40-nm thick were formed on a glass substrate. A disk was formed by bonding 2 substrates prepared on the sides of Si3N4 protective films using a UV-cured resin. A signal output >100 mV was obtained.